



# PSMN4R3-40MSH

N-channel 40 V, 4.3 mΩ, standard level MOSFET in LFAK33 using NextPower-S3 technology

27 April 2020

Product data sheet

## 1. General description

95 A, standard level N-channel enhancement mode MOSFET in 175 °C LFAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low  $Q_{RR}$ ,  $Q_G$  and  $Q_{GD}$  for high system efficiency, especially at high switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

## 3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

## 4. Quick reference data

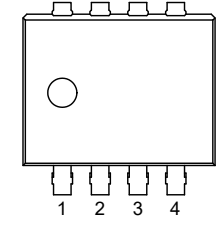
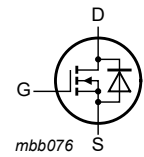
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	[1]	-	95	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	90	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	3.5	4.3	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>	1.1	3.6	7.3	nC
$Q_{G(tot)}$	total gate charge		15	23	32	nC

[1] 95A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	Mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-40MSH	LPAK33	Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R3-40MSH	4H3S40

## 8. Limiting values

Table 5. Limiting values

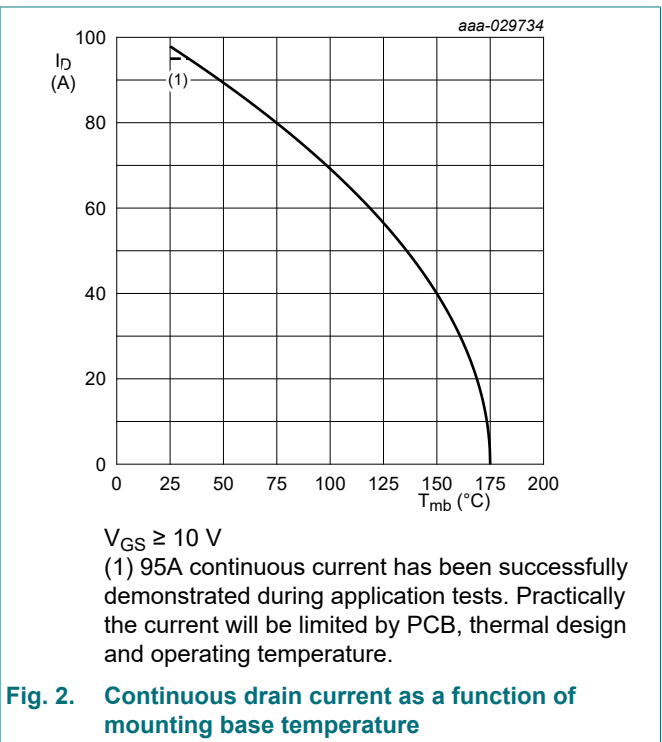
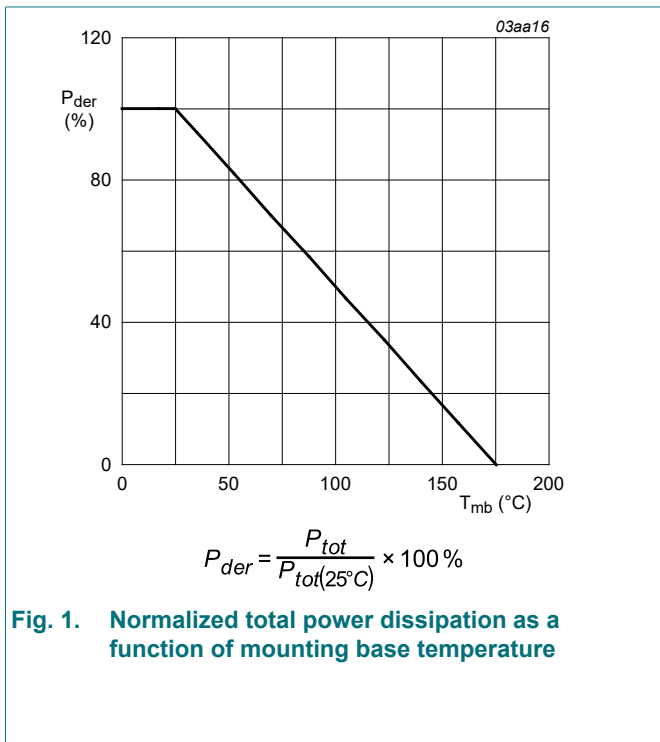
In accordance with the Absolute Maximum Rating System (IEC 60134).

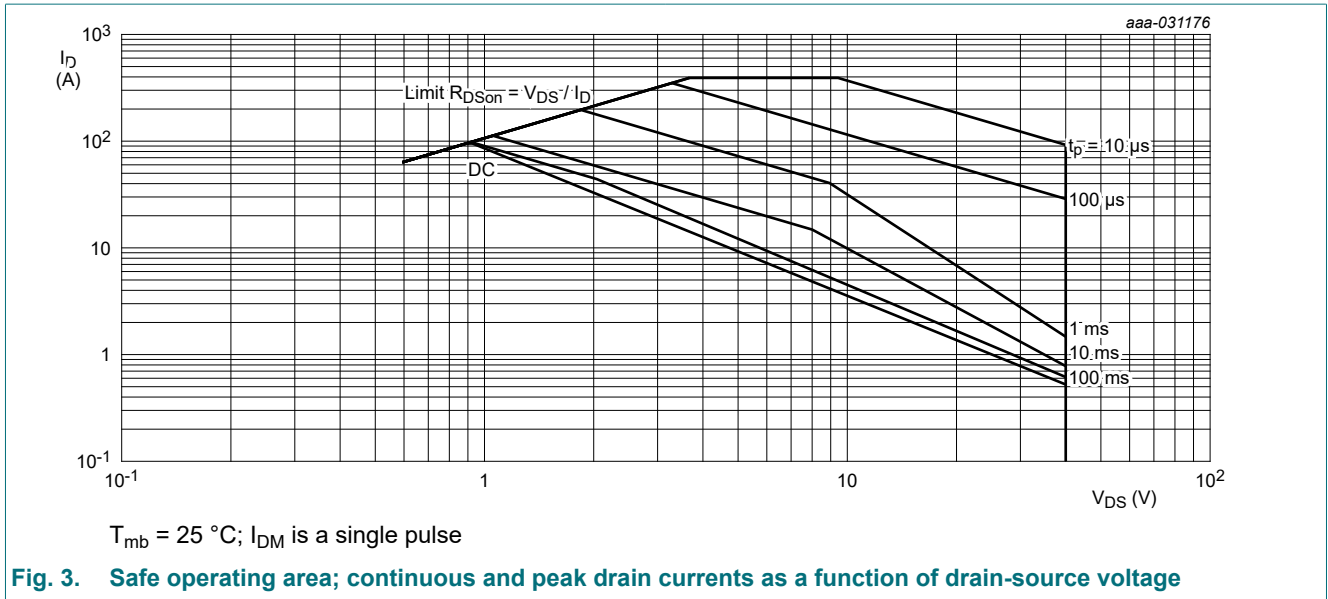
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	40	V
$V_{DSM}$	peak drain-source voltage	$t_p \leq 20\text{ ns}$ ; $f \leq 500\text{ kHz}$ ; $E_{DS(AL)} \leq 200\text{ nJ}$ ; pulsed	-	45	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	40	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	90	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	[1]	95	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>	-	69	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>	-	392	A
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	95	A

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Symbol	Parameter	Conditions		Min	Max	Unit
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \mu s$ ; $T_{mb} = 25^\circ C$		-	392	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 32.6 A$ ; $V_{sup} \leq 40 V$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 V$ ; $T_{j(init)} = 25^\circ C$ ; unclamped; $t_p = 117 \mu s$	[2]	-	99	mJ
		$I_D = 25 A$ ; $V_{sup} \leq 40 V$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 V$ ; $T_{j(init)} = 25^\circ C$ ; unclamped; $t_p = 204 \mu s$	[2]	-	132	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} \leq 40 V$ ; $V_{GS} = 10 V$ ; $T_{j(init)} = 25^\circ C$ ; $R_{GS} = 50 \Omega$	[2]	-	70	A

- [1] 95A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test

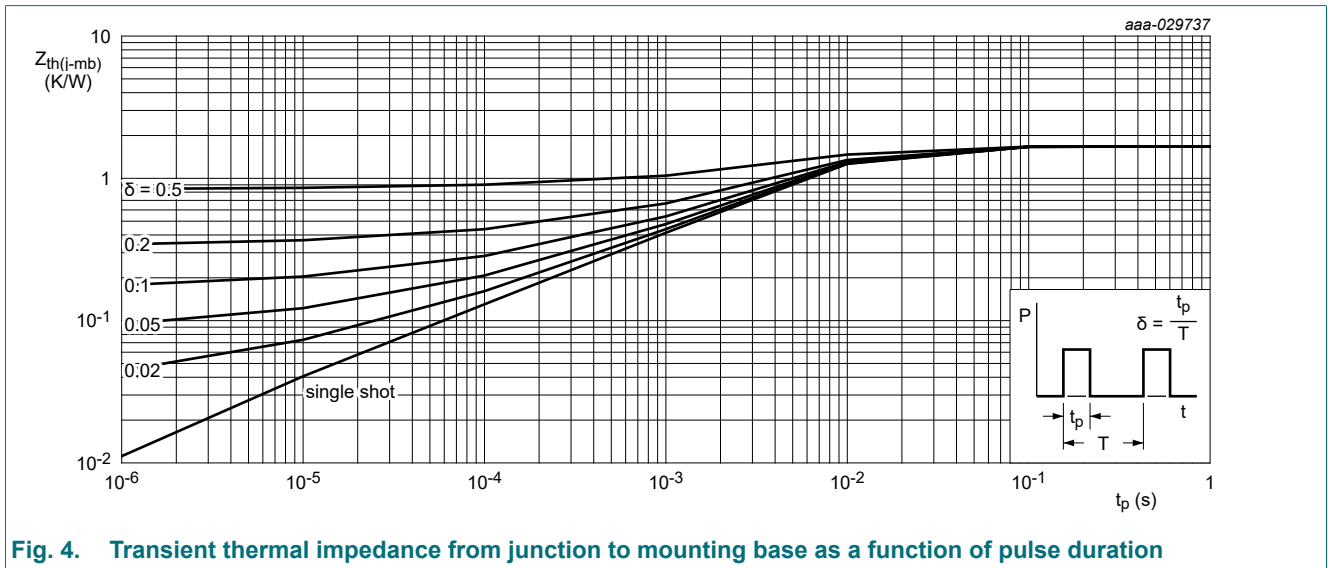


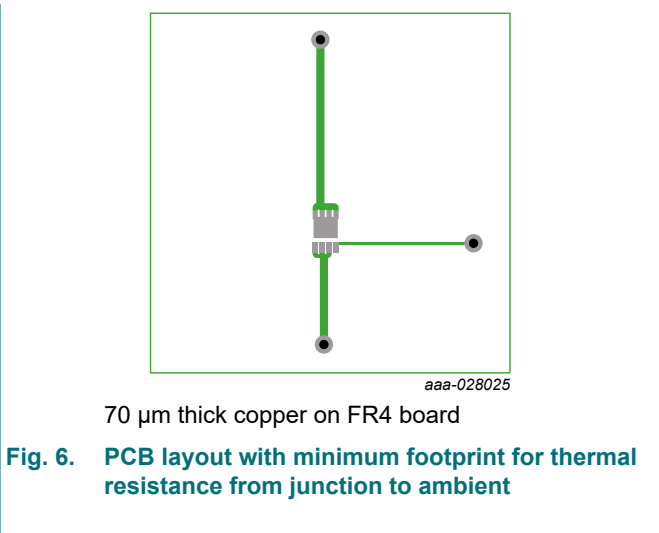
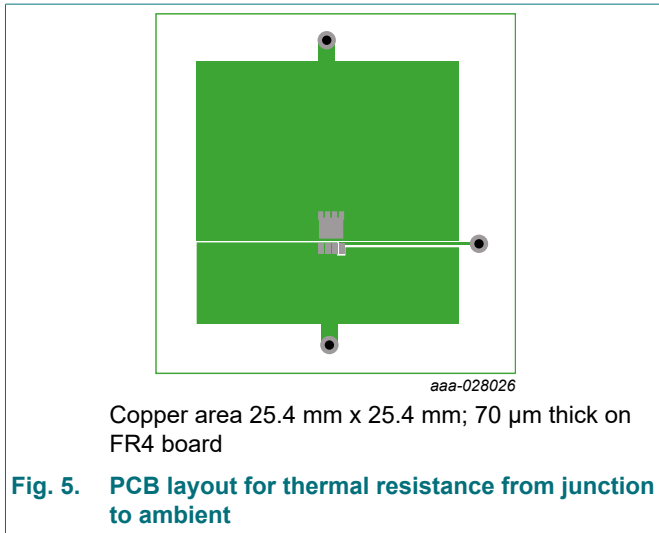


### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	1.48	1.67	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	130	-	K/W





## 10. Characteristics

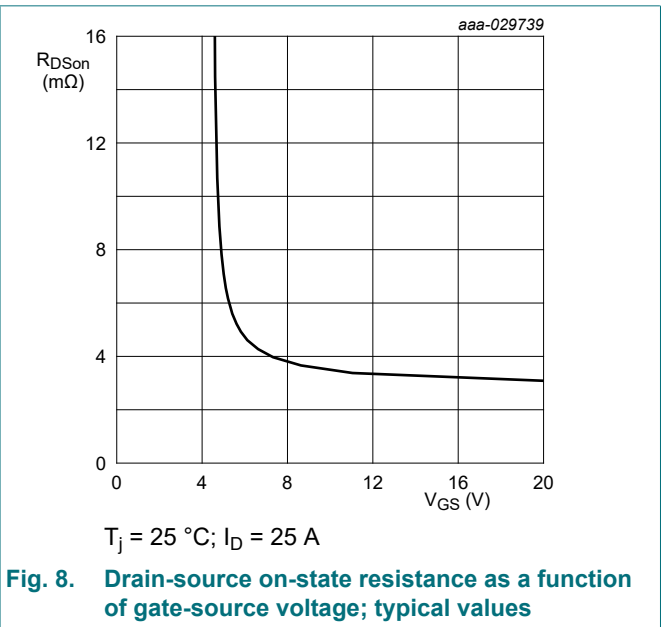
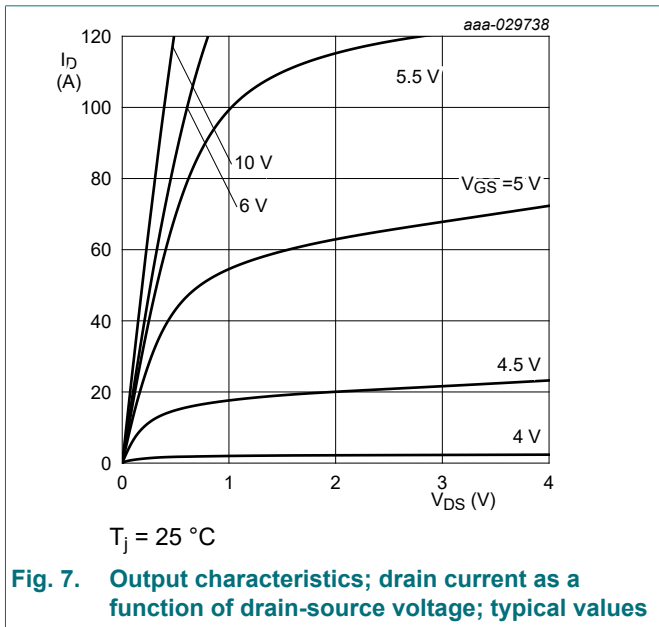
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	2.4	3	3.6	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-5.9	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.01	1	μA
		$V_{DS} = 32 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	2	-	μA
$I_{GSS}$	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10</a>	-	3.5	4.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 11</a>	-	-	9.4	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	0.3	0.8	2	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	15	23	32	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	12.3	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	4.4	7.3	11	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		2.8	4.7	7	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		1.5	2.6	3.8	nC
$Q_{GD}$	gate-drain charge		1.1	3.6	7.3	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	4.5	-	V

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$C_{iss}$	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a>	1086	1670	2338	pF	
$C_{oss}$	output capacitance		363	559	782	pF	
$C_{rss}$	reverse transfer capacitance		25	83	182	pF	
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20\text{ V}; R_L = 0.8\text{ }^\Omega; V_{GS} = 10\text{ V}; R_{G(ext)} = 5\text{ }^\Omega$	-	6.5	-	ns	
$t_r$	rise time		-	4.5	-	ns	
$t_{d(off)}$	turn-off delay time		-	12.4	-	ns	
$t_f$	fall time		-	4.4	-	ns	
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 20\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$	-	17.2	-	nC	
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 15</a>	-	0.83	1	V	
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V}; V_{DS} = 20\text{ V};$ <a href="#">Fig. 16</a>	-	26	-	ns	
$Q_r$	recovered charge		[1]	-	20	-	nC
$t_a$	reverse recovery rise time		-	-	16	-	ns
$t_b$	reverse recovery fall time		-	-	10	-	ns

[1] includes capacitive recovery



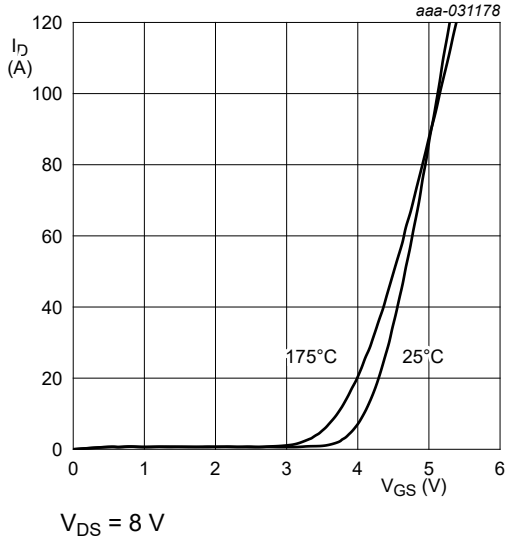


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

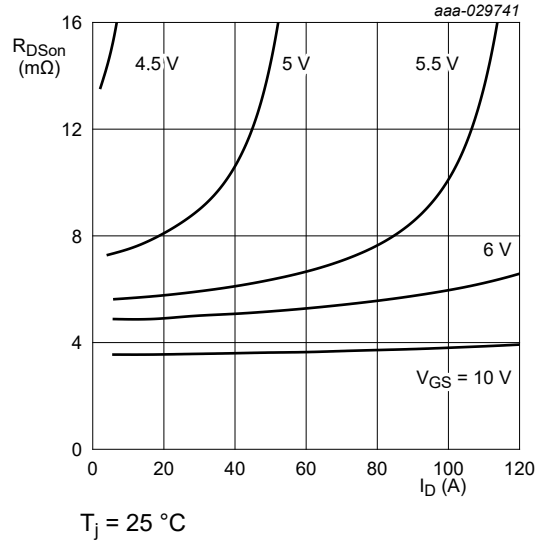


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

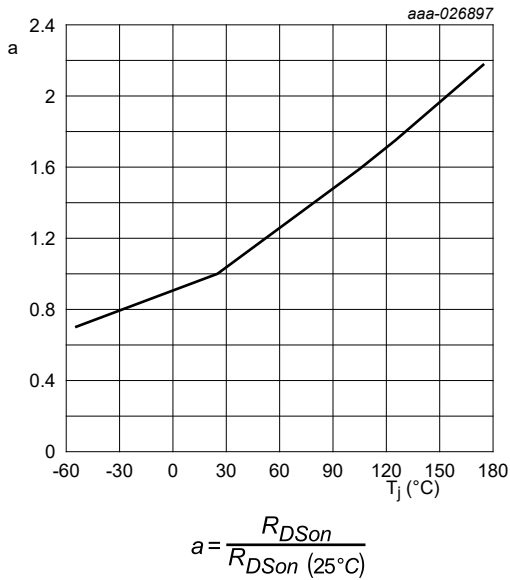


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

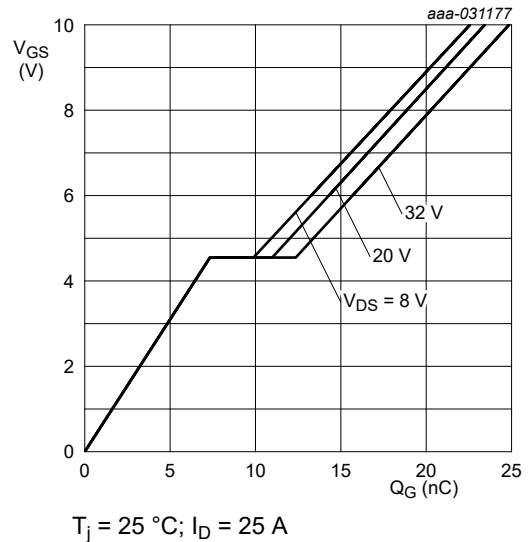


Fig. 12. Gate-source voltage as a function of gate charge; typical values

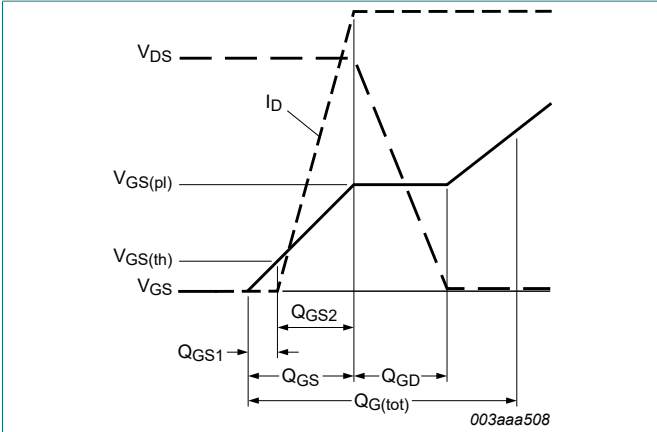


Fig. 13. Gate charge waveform definitions

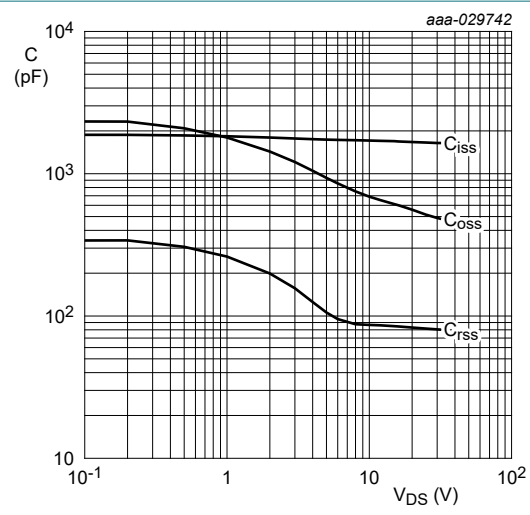


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values  
 $V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

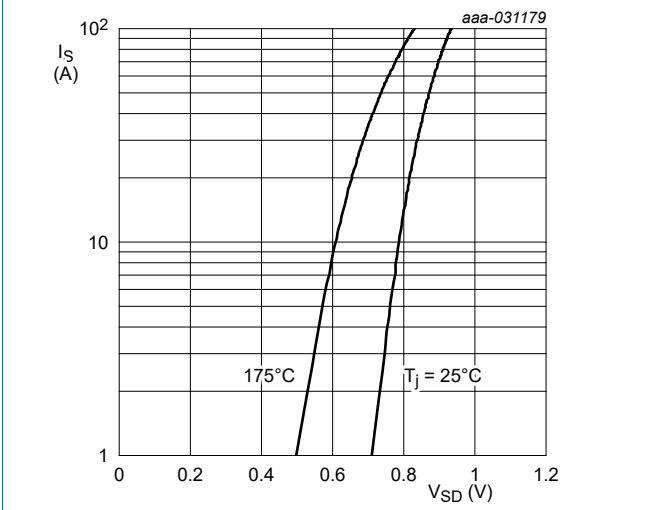


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values  
 $V_{GS} = 0 \text{ V}$

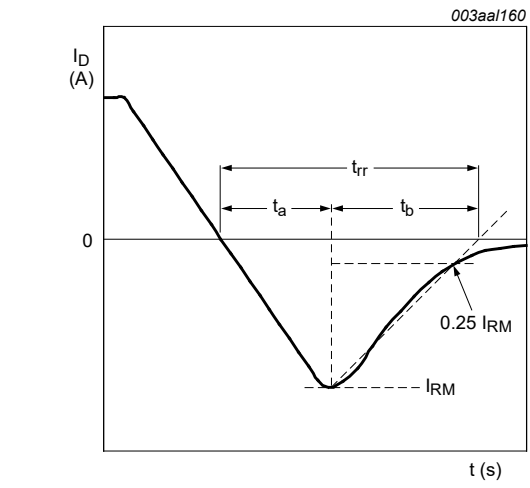


Fig. 16. Reverse recovery timing definition



11. Package outline

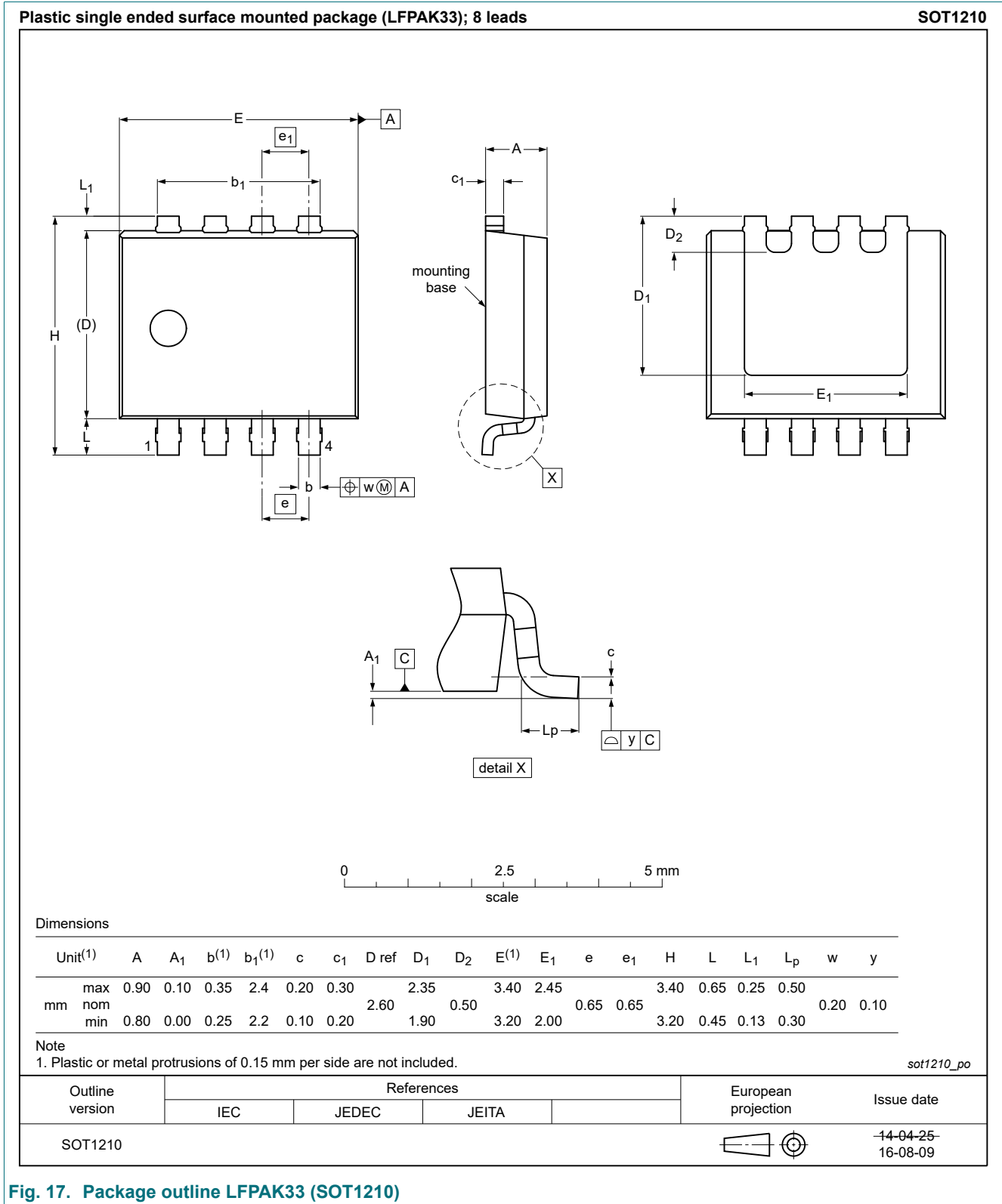
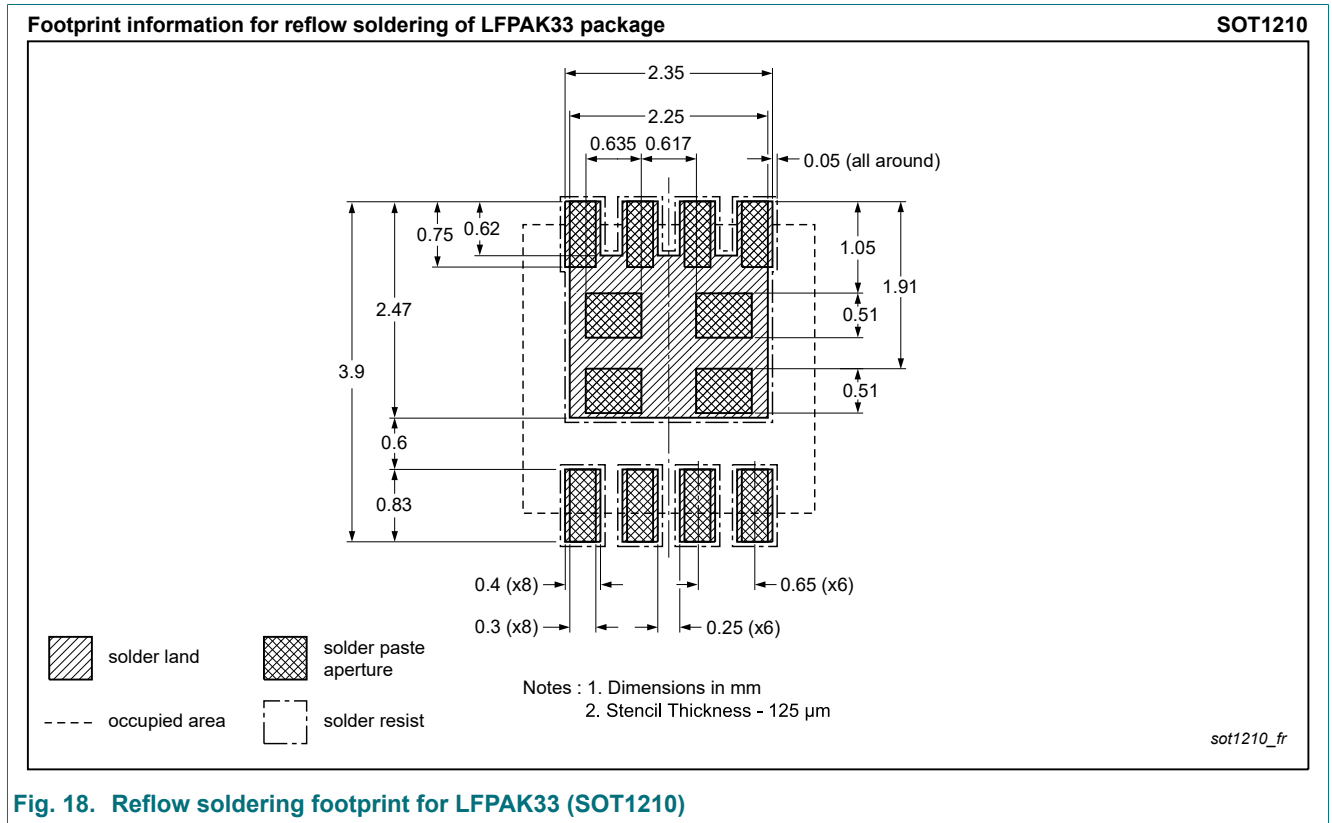


Fig. 17. Package outline LPAK33 (SOT1210)

## 12. Soldering



**Fig. 18. Reflow soldering footprint for LPAK33 (SOT1210)**

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 27 April 2020

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